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ABSTRACT OF THE DISCLOSURE

A semiconductor device is provided with an SRAM memory cell. The semiconductor device includes a first gate-gate electrode layer, a second gate-gate electrode layer, a first drain-drain wiring layer, a second drain-drain wiring layer, a first drain-gate wiring layer and second drain-gate wiring layers. The first drain-gate wiring layer and an upper layer and a lower layer of the second drain-gate wiring layer are located in different layers, respectively. A first protruded active region is provided in a manner to protrude from an end portion of the first active region.

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